

### NCE P-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE3401AY uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

#### **General Features**

•  $V_{DS} = -30V, I_{D} = -4.4A$ 

 $R_{DS(ON)}$  <  $80m\Omega$  @  $V_{GS}$ =-2.5V

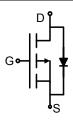
 $R_{DS(ON)}$  < 65m $\Omega$  @  $V_{GS}$ =-4.5V

 $R_{DS(ON)}$  < 52m $\Omega$  @  $V_{GS}$ =-10V

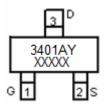
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

### **Application**

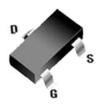
- PWM applications
- Load switch
- Power management



#### Schematic diagram



#### Marking and pin Assignment



SOT-23-3L top view

#### **Package Marking And Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3401AY	NCE3401AY	SOT-23-3L	Ø180mm	8 mm	3000 units

#### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current-Continuous	I <sub>D</sub>	-4.4	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	-30	Α
Maximum Power Dissipation	P <sub>D</sub>	1.3	W
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}$ C

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	R <sub>θJA</sub>	95	°C/W
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#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V



# http://www.ncepower.com

# NCE3401AY

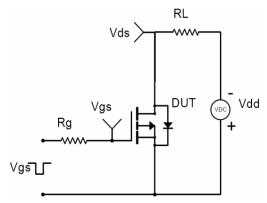
Parameter	Symbol	Condition	Min	Тур	Max	Unit		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μΑ		
Gate-Body Leakage Current	I <sub>GSS</sub> V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V		-	-	±100	nA		
On Characteristics (Note 3)								
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.7	-1	-1.3	V		
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	-	39	52	mΩ		
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	46	65	mΩ		
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A		61	80	mΩ		
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-2A	-	10	-	S		
Dynamic Characteristics (Note4)								
Input Capacitance	C <sub>Iss</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V.	-	950	-	PF		
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =UV, F=1.0MHz	-	115	-	PF		
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0lvlH2	-	75	-	PF		
Switching Characteristics (Note 4)	Switching Characteristics (Note 4)							
Turn-on Delay Time	t <sub>d(on)</sub>		-	7	-	nS		
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-15V,I <sub>D</sub> =-3.2A	-	3	-	nS		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{GEN}$ =6 $\Omega$	-	30	-	nS		
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS		
Total Gate Charge	Qg		-	9.5	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4A,V <sub>GS</sub> =-4.5V	-	2	-	nC		
Gate-Drain Charge	$Q_{gd}$		-	3	-	nC		
Drain-Source Diode Characteristics								
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1A	-	-	-1.2	V		

## Notes:

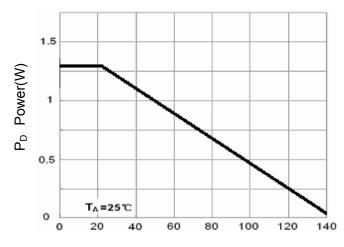
- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**

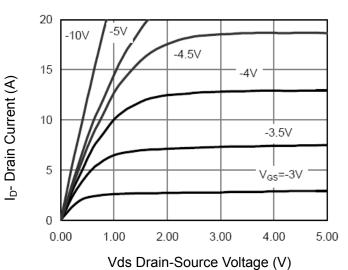


**Figure 1:Switching Test Circuit** 

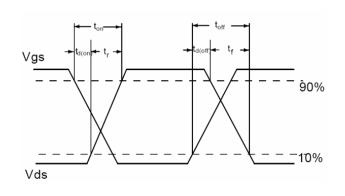


T<sub>J</sub>-Junction Temperature(°C)

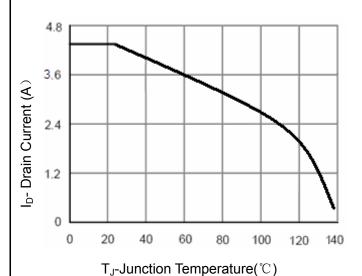
**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 



**Figure 2:Switching Waveforms** 



**Figure 4 Drain Current** 

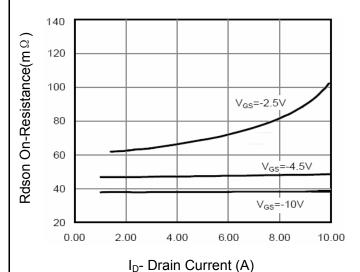
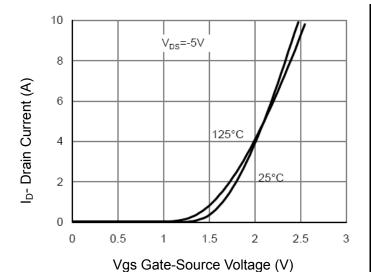
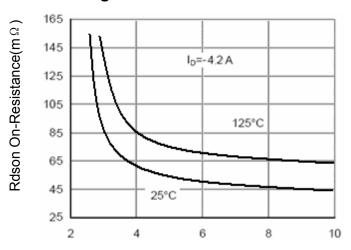


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

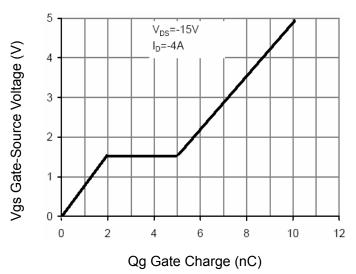
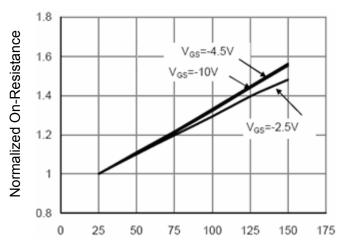
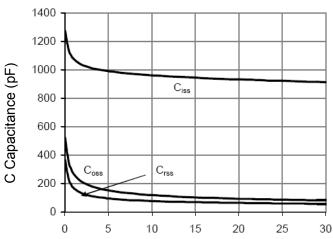


Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(°C)





Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

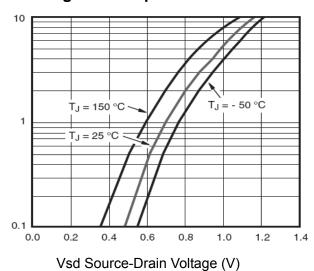
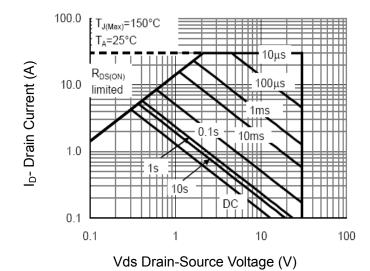


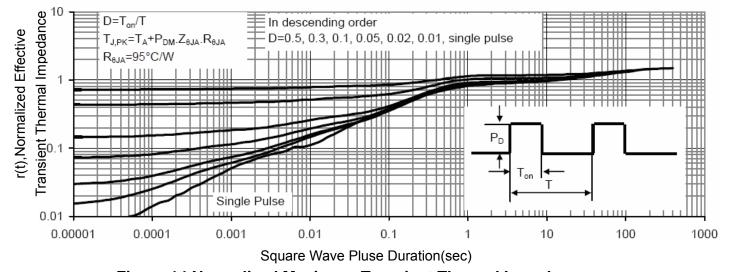
Figure 12 Source- Drain Diode Forward

Is- Reverse Drain Current (A)





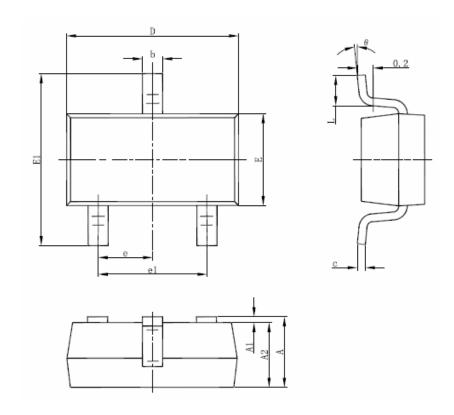
**Figure 13 Safe Operation Area** 



**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23-3L Package Information**



Sumb a l	Dimensions In	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
Е	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037(	BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

#### **Notes**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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